

1. Scope

The present specifications shall apply to an SJPZ-E33.

2. Outline

Type	Silicon Diode
Structure	Resin Molded
Applications	Over Voltage Absorption

3. Flammability

UL94V-0 (Equivalent)

Not Recommended for New Designs

4. Absolute maximum ratings

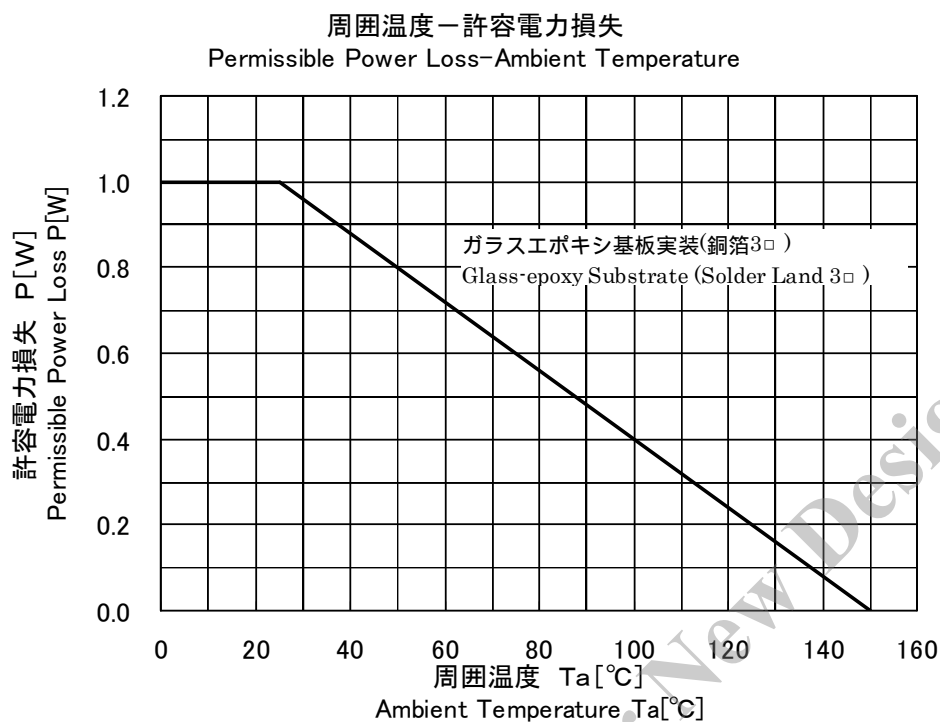
No.	Item	Symbol	Unit	Rating	Conditions
1	Permissible Power loss	P	W	1	Refer to Derating of 6
2	Transient Peak Reverse Power	P _{RSM}	W	95	Single Square Wave
3	Junction Temperature	T _j	°C	-55~+150	—
4	Storage Temperature	T _{stg}	°C	-55~+150	—

5. Electrical characteristics(Ta=25°C , unless otherwise specified)

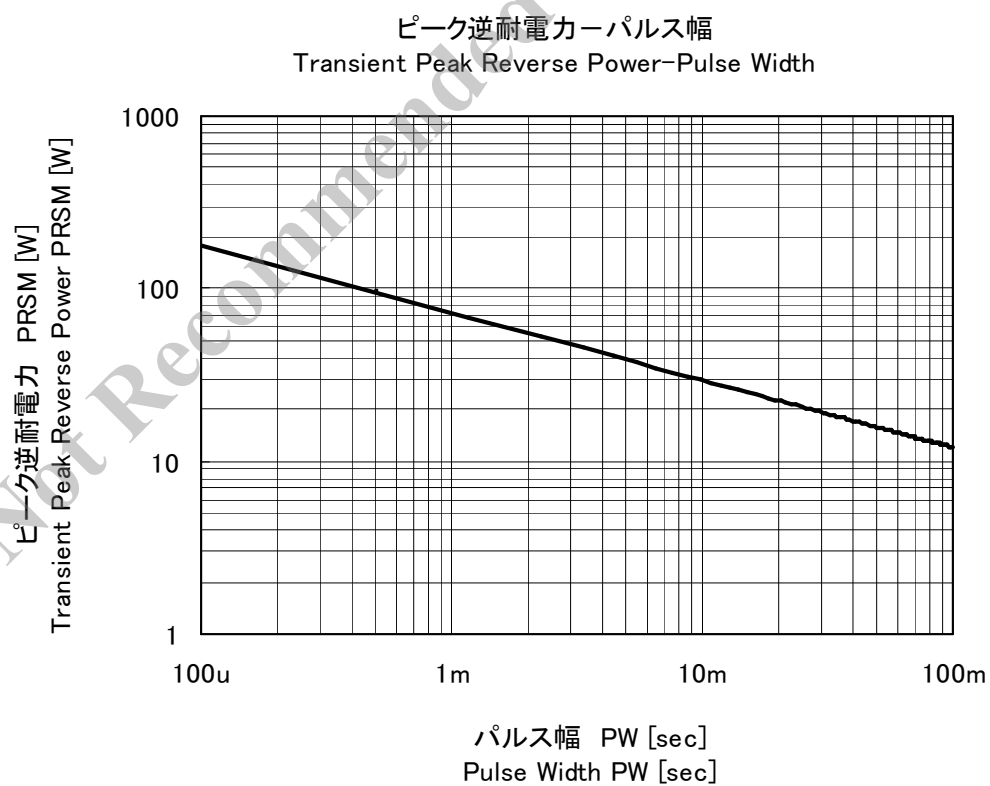
No.	Item	Symbol	Unit	Value	Conditions
1	Reverse Breakdown Voltage	V _Z	V	31.0 ~ 35.0	I _Z =1mA
2	Reverse Leakage Current	I _R	uA	10 max.	V _R =25V
3	Temperature Coefficient Breakdown Voltage	γ _z	mV/°C	28 typ.	I _Z =1mA
4	Equivalent Resistance of Breakdown Region	R _Z	Ω	10 typ.	I _Z =10mA ~ 20mA

6. Derating

Permissible Power Loss

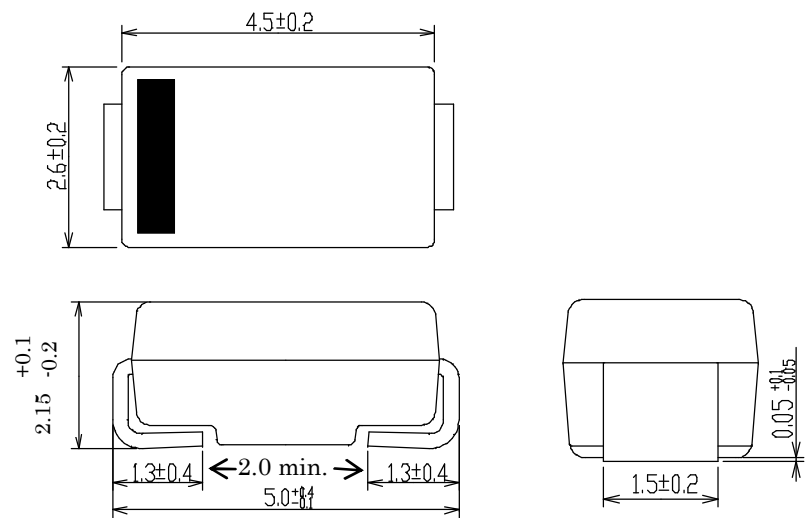


7. Transient Peak Reverse Power Rating



8. Package information

8-1 Package type, physical dimensions

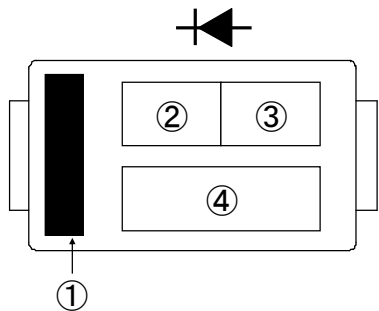


Dimensions in mm

8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking



① Polarity marking (Cathode band)

② Type number
SJPZ-E as abbreviated of ZE.

③ Vz Class number
33V as abbreviated of 33.

④ Lot number
Example) 6508
6: Last number of Year
5: Month from 1 to 9 for Jan. to Sep. O for Oct. , N for Nov. , D for Dec.
08: Day.